



PATENT APPLICATION
Do. No. 5484-093

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Byeong-Hoon LEE and Seung-Keun LEE

Serial No. 09/997,080

Examiner: Phan, Trong Q

Filed: November 28, 2001

Group Art Unit: 2818

For: NONVOLATILE SEMICONDUCTOR MEMORY DEVICE

Confirmation No. 6095

BOX RCE
Assistant Commissioner for Patents
Washington, D.C. 20231

REQUEST FOR CONTINUED EXAMINATION

Responsive to the Final Office Action mailed November 14, 2002, and the Advisory Action, mailed January 29, 2003, please amend the application as follows.

IN THE CLAIMS

Please replace the claims with the following set, in which claims 1, 10, 15, and 18 are amended and claims 26 and 27 are new.

- Sub D1*
1. (Amended) A nonvolatile semiconductor memory device comprising:
- a substrate;
 - a plurality of sectors on the substrate;
 - each sector comprising memory cell transistors arranged in a cell array block and decoder transistors in a column decoder block;
- C1*
- wherein the transistors in the cell array block and column decoder block in each sector share a common bulk region, wherein the common bulk region is formed on the substrate and is connected to a bulk driver provided in each of the sectors, each said bulk driver configured to commonly apply a bulk voltage to the common bulk region of the sector; and
 - wherein said semiconductor memory device is configured to electrically erase all the memory cell transistors in a sector together.

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